Search History

STN
(HCAPLUS, INSPEC, JAPIO, USPATALL)
4/11/06

=> d l14 1-8 abs,bib

L14 ANSWER 1 OF 8 USPATFULL on STN
AB A process for preparing p-n or n-p junctions having a p-type oxide **film** is disclosed. In one embodiment, a **p-type zinc oxide film** has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2004:124122 USPATFULL
TI Process for preparing p-n junctions having a **p-type ZnO film**
IN White, Henry W., Columbia, MO, UNITED STATES
Zhu, Shen, Huntsville, AL, UNITED STATES
Ryu, Yungryel, Columbia, MO, UNITED STATES
PA The Curators of the University of Missouri (U.S. corporation)
PI US 2004094085 A1 20040520
AI US 2003-615102 A1 20030708 (10)
RLI Continuation of Ser. No. US 2001-2790, filed on 15 Nov 2001, GRANTED, Pat. No. US 6610141 Division of Ser. No. US 1999-439529, filed on 12 Nov 1999, GRANTED, Pat. No. US 6342313 Continuation-in-part of Ser. No. US 1999-364809, filed on 30 Jul 1999, GRANTED, Pat. No. US 6410162 Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998, GRANTED, Pat. No. US 6291085
DT Utility
FS APPLICATION
LREP SENNIGER POWERS LEAVITT AND ROEDEL, ONE METROPOLITAN SQUARE, 16TH FLOOR, ST LOUIS, MO, 63102
CLMN Number of Claims: 77
ECL Exemplary Claim: 1
DRWN 9 Drawing Page(s)
LN.CNT 1049
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 2 OF 8 USPATFULL on STN
AB A **p-type zinc oxide film** and a process for preparing the **film** and p-n or n-p junctions is disclosed. In a preferred embodiment, the **p-type zinc oxide film** contains arsenic and is grown on a gallium arsenide substrate. The **p-type zinc oxide film** has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:152321 USPATFULL
TI **Zinc oxide films** containing **p-type** dopant and process for preparing same
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States
PA The Curators of the University of Missouri, Columbia, MO, United States (U.S. corporation)
PI US 6410162 B1 20020625
AI US 1999-364809 19990730 (9)
RLI Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998, now patented, Pat. No. US 6291085
DT Utility
FS GRANTED
EXNAM Primary Examiner: Lam, Cathy
LREP Senniger, Powers, Leavitt & Roedel
CLMN Number of Claims: 25
ECL Exemplary Claim: 1
DRWN 10 Drawing Figure(s); 9 Drawing Page(s)
LN.CNT 804

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 3 OF 8 USPATFULL on STN
AB A p-type oxide film and a process for preparing the film and p-n or n-p junctions is disclosed. In a preferred embodiment, a **p-type zinc oxide film** contains arsenic and is grown on a gallium arsenide substrate. The p-type oxide film has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:105800 USPATFULL
TI **Zinc oxide films** containing **p-type** dopant and process for preparing same
IN White, Henry W., Columbia, MO, UNITED STATES
Zhu, Shen, Huntsville, AL, UNITED STATES
Ryu, Yungryel, Columbia, MO, UNITED STATES
PA The Curators of the University of Missouri (U.S. corporation)
PI US 2002055003 A1 20020509
US 6610141 B2 20030826
AI US 2001-2790 A1 20011115 (10)
RLI Division of Ser. No. US 1999-439529, filed on 12 Nov 1999, PATENTED Continuation-in-part of Ser. No. US 1999-364809, filed on 30 Jul 1999, PENDING Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998, PATENTED
DT Utility
FS APPLICATION
LREP SENNIGER POWERS LEAVITT AND ROEDEL, ONE METROPOLITAN SQUARE, 16TH FLOOR, ST LOUIS, MO, 63102
CLMN Number of Claims: 81
ECL Exemplary Claim: 1
DRWN 9 Drawing Page(s)
LN.CNT 1060
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 4 OF 8 USPATFULL on STN
AB A **p-type zinc oxide film** and a process for preparing the **film** is disclosed. In a preferred embodiment, the **p-type zinc oxide film** contains arsenic and is grown on a gallium arsenide substrate. The **p-type zinc oxide film** has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:54520 USPATFULL
TI **Zinc oxide films** containing **p-type** dopant and process for preparing same
IN White, Henry W., Columbia, MO, UNITED STATES
Zhu, Shen, Huntsville, AL, UNITED STATES
Ryu, Yungryel, Columbia, MO, UNITED STATES
PI US 2002031680 A1 20020314
US 6475825 B2 20021105
AI US 2001-843205 A1 20010426 (9)
RLI Division of Ser. No. US 1998-128516, filed on 3 Aug 1998, GRANTED, Pat. No. US 6291085
DT Utility
FS APPLICATION
LREP SENNIGER POWERS LEAVITT AND ROEDEL, ONE METROPOLITAN SQUARE, 16TH FLOOR, ST LOUIS, MO, 63102
CLMN Number of Claims: 50
ECL Exemplary Claim: 1
DRWN 4 Drawing Page(s)
LN.CNT 692

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 5 OF 8 USPATFULL on STN
AB A p-type oxide film and a process for preparing the film and p-n or n-p junctions is disclosed. In a preferred embodiment, a **p-type zinc oxide film** contains arsenic and is grown on a gallium arsenide substrate. The p-type oxide film has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:19144 USPATFULL
TI Oxide films and process for preparing same
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States
PA The Curators of the University of Missouri, Columbia, MO, United States (U.S. corporation)
PI US 6342313 B1 20020129
AI US 1999-439529 19991112 (9)
RLI Continuation-in-part of Ser. No. US 1999-364809, filed on 30 Jul 1999
Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998, now patented, Pat. No. US 6291085
DT Utility
FS GRANTED
EXNAM Primary Examiner: Jones, Deborah; Assistant Examiner: de la Pena, Jason
LREP Senniger, Powers, Leavitt & Roedel
CLMN Number of Claims: 13
ECL Exemplary Claim: 1
DRWN 10 Drawing Figure(s); 9 Drawing Page(s)
LN.CNT 807
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 6 OF 8 USPATFULL on STN
AB A **p-type zinc oxide film** and a process for preparing the **film** is disclosed. In a preferred embodiment, the **p-type zinc oxide film** contains arsenic and is grown on a gallium arsenide substrate. The **p-type zinc oxide film** has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2 /Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2001:157919 USPATFULL
TI **Zinc oxide films** containing **p-type** dopant and process for preparing same
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States
PA The Curators of the University of Missouri, Columbia, MO, United States (U.S. corporation)
PI US 6291085 B1 20010918
AI US 1998-128516 19980803 (9)
DT Utility
FS GRANTED
EXNAM Primary Examiner: Lorin, Francis J.
LREP Senniger, Powers, Leavitt & Roedel
CLMN Number of Claims: 30
ECL Exemplary Claim: 1
DRWN 5 Drawing Figure(s); 4 Drawing Page(s)
LN.CNT 608
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 7 OF 8 USPAT2 on STN

AB A p-type oxide film and a process for preparing the film and p-n or n-p junctions is disclosed. In a preferred embodiment, a **p-type zinc oxide film** contains arsenic and is grown on a gallium arsenide substrate. The p-type oxide film has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:105800 USPAT2
TI **Zinc oxide films** containing **p-type** dopant and process for preparing same
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States
PA The Curators of the University of Missouri, Columbia, MO, United States (U.S. corporation)
PI US 6610141 B2 20030826
AI US 2001-2790 20011115 (10)
RLI Division of Ser. No. US 1999-439529, filed on 12 Nov 1999, now patented, Pat. No. US 6342313 Continuation-in-part of Ser. No. US 1999-364809, filed on 30 Jul 1999 Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998, now patented, Pat. No. US 6291085
DT Utility
FS GRANTED
EXNAM Primary Examiner: Hiteshew, Felisa
LREP Senniger, Powers, Leavitt & Roedel
CLMN Number of Claims: 40
ECL Exemplary Claim: 1
DRWN 10 Drawing Figure(s); 9 Drawing Page(s)
LN.CNT 976
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 8 OF 8 USPAT2 on STN
AB A **p-type zinc oxide film** and a process for preparing the **film** is disclosed. In a preferred embodiment, the **p-type zinc oxide film** contains arsenic and is grown on a gallium arsenide substrate. The **p-type zinc oxide film** has a **net acceptor concentration** of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:54520 USPAT2
TI Process for preparing **zinc oxide films** containing **p-type** dopant
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States
PA The Curators of the University of Missouri, Columbia, MO, United States (U.S. corporation)
PI US 6475825 B2 20021105
AI US 2001-843205 20010426 (9)
RLI Division of Ser. No. US 1998-128516, filed on 3 Aug 1998, now patented, Pat. No. US 6291085
DT Utility
FS GRANTED
EXNAM Primary Examiner: Sherry, Michael; Assistant Examiner: Pert, Evan
LREP Senniger, Powers, Leavitt & Roedel
CLMN Number of Claims: 24
ECL Exemplary Claim: 1
DRWN 5 Drawing Figure(s); 4 Drawing Page(s)
LN.CNT 660
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

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     (FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2' ENTERED AT 06:07:43 ON
     11 APR 2005)
                DELETE HIS
L1          19321 S (ZNO OR ZINC(W)OXIDE)(8A)(FILM#)
L2            248 S (NET(W)ACCEPTOR#)(8A)(CONCENTRATION#)
L3         146133 S (CLEAN? OR ETCH?)(6A)(SUBSTRATE#)
L4           8512 S (ADJUST? OR MANIPULAT? OR CHANG? OR ALTER?)(8A)(TEMPERATURE(6
L5         190433 S (PULS?(6A)LASER)
L6            315 S (P(W)TYPE)(8A)(ZNO(4A)FILM# OR ZINC(W)OXIDE(4A)FILM#)
L7             41 S (PELLET#)(8A)(PRESS?(6A)ZNO OR PRESS(6A)ZINC(W)OXIDE)
L8        1321353 S (POWDER#)
L9             10 S L1 AND L2
L12             8 S L1 AND L2 AND L3 AND L4 AND L5 AND L6
L13             8 S L7 AND L12
L14             8 S L1 AND L2 AND L3 AND L4 AND L5 AND L6 AND L7 AND L8

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Day : Monday
Date: 4/11/2005

PALM INTRANET

Time: 11:12:56

Inventor Name Search Result

Your Search was:

Last Name = WHITE
First Name = HENRY W.

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09364809	6410162	150	07/30/1999	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	WHITE, HENRY W.
09439529	6342313	150	11/12/1999	OXIDE FILMS AND PROCESS FOR PREPARING SAME	WHITE, HENRY W.

Inventor Search Completed: No Records to Display.

Search Another: Inventor Last Name: White First Name: Henry W. Search

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Day : Monday
Date: 4/11/2005

PALM INTRANET

Time: 11:13:26

Inventor Name Search Result

Your Search was:

Last Name = ZHU
First Name = SHEN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09128516	6291085	150	08/03/1998	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
09364809	6410162	150	07/30/1999	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
09439529	6342313	150	11/12/1999	OXIDE FILMS AND PROCESS FOR PREPARING SAME	ZHU, SHEN
09843205	6475825	150	04/26/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
10002790	6610141	150	11/15/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
10615102	Not Issued	030	07/08/2003	PROCESS FOR PREPARING P-N JUNCTIONS HAVING A P-TYPE ZNO FILM	ZHU, SHEN
09075555	6022261	150	05/08/1998	VERTICALLY SINKABLE TOY SHIP MODEL	ZHU, SHENG BO
07436885	Not Issued	161	11/14/1989	METHOD FOR PRODUCING A NON-MAXWELLIAN KINETIC ENERGY DISTRIBUTION IN A COLLECTION OF LOW-MASS PARTICLES	ZHU, SHENG-BAI
11052725	Not Issued	020	02/07/2005	SOLID-STATE LASERS EMPLOYING INCOHERENT MONOCHROMATIC PUMP	ZHU, SHENG-HAI
07455070	5126971	150	12/22/1989	THIN FILM MAGNETIC CORE MEMORY AND METHOD OF	ZHU, SHENGBO

				MAKING SAME	
07463567	5072324	150	01/11/1990	THIN FILM TRANSDUCER/TRANSFORMER ASSEMBLY	ZHU, SHENGBO
07772981	Not Issued	166	10/07/1991	MINIATURE TRANSDUCER/SIGNAL BOOSTER ASSEMBLY	ZHU, SHENGBO
07781713	Not Issued	166	10/22/1991	THIN FILM TRANSDUCER WITH COIL GUARD SEGMENT	ZHU, SHENGBO
07847765	Not Issued	161	03/05/1992	MAGNETIC SLIDER WITH IMPROVED SUBSTRATE MATERIAL	ZHU, SHENGBO
07847770	5305168	150	03/05/1992	THIN FILM TRANSDUCER SUSPENION ASSEMBLY WITH FLEXURE-MOUNTED BOOSTER ELEMENT	ZHU, SHENGBO
07878701	5831800	250	05/05/1992	MINIATURE TRANSFORMER FOR READ/WRITE TRANSDUCER	ZHU, SHENGBO
07879405	Not Issued	166	05/05/1992	MINIATURE THIN FILM INDUCTIVE DEVICE WITH ADDITIONAL MAGNETIC MATERIAL IN THE CONTACT REGION BETWEEN POLE PIECES	ZHU, SHENGBO
07998751	Not Issued	161	12/29/1992	MINIATURE TRANSDUCER/TRANSFORMER ASSEMBLY	ZHU, SHENGBO
08071787	Not Issued	161	06/04/1993	THIN FILM TRANSDUCER WITH REDUCED FLYING HEIGHT	ZHU, SHENGBO
08193667	Not Issued	161	02/08/1994	THIN FILM TRANSDUCER WITH COIL GUARD SEGMENT	ZHU, SHENGBO
08193668	Not Issued	161	02/08/1994	MINIATURE THIN FILM INDUCTIVE DEVICE WITH ADDITIONAL MAGNETIC MATERIALIN THE CONTACT REGION BETWEEN POLE PIECES	ZHU, SHENGBO
08322030	Not Issued	166	10/12/1994	THIN FILM TRANSDUCER WITH REDUCED FLYING HEIGHT	ZHU, SHENGBO
08651438	Not Issued	161	05/22/1996	THIN FILM TRANSDUCER WITH REDUCED FLYING HEIGHT	ZHU, SHENGBO
08685290	Not Issued	161	07/23/1996	ELECTRIC FAN COOLING SYSTEM WITH TEMPERATURE SENSED SPEED CONTROL	ZHU, SHENGBO

08886271	Not Issued	169	07/01/1997	HELICAL PLANAR HEAD	ZHU, SHENGBO
09115728	6360953	150	07/15/1998	SECURE PRINT SENSING SMART CARD WITH ON-THE-FLY-OPERATION	ZHU, SHENGBO
09131798	Not Issued	161	08/10/1998	VOICE RESPONSIVE PAPER SHREDDER WITH DECORATIVE CASING	ZHU, SHENGBO
09144391	5977875	150	08/31/1998	COLLECTIVE OBJECTS MANAGEMENT SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
09161175	Not Issued	161	09/25/1998	INVENTORY CONTROL SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
09506509	6819222	150	02/17/2000	INVENTORY CONTROL SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
09506652	6791398	150	02/17/2000	DATA TOKEN WITH POWER SAVING SWITCH	ZHU, SHENGBO
09541672	6567010	150	03/31/2000	TRAFFIC SIGNAL HEAD WITH MULTIPLE LED ILLUMINATION SOURCES	ZHU, SHENGBO
09565992	6348864	150	05/06/2000	ORGANIZER MANAGEMENT SYSTEM USING R.F. IDENTIFICATION	ZHU, SHENGBO
09751198	6664895	150	01/02/2001	R.F. SUPPRESSION TECHNIQUE FOR COLLECTIVE OBJECTS MANAGEMENT SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
10900485	Not Issued	030	07/28/2004	MULTI-PHASE A.C. VEHICLE MOTOR	ZHU, SHENGBO
10804811	Not Issued	030	03/19/2004	IDENTIFYING EARLY ADOPTERS AND ITEMS ADOPTED BY THEM	ZHU, SHENGHUO
09235190	6297507	150	01/22/1999	SEALED TUBE NEUTRON GENERATOR INCORPORATING AN INTERNAL ASSOCIATED-ALP	ZHU, SHENGJIANG

Inventor Search Completed: No Records to Display.

Search Another: Inventor **Last Name** Zhu **First Name** Shen Search

To go back use Back button on your browser toolbar.

Day : Monday
Date: 4/11/2005

PALM INTRANET

Time: 11:13:47

Inventor Name Search Result

Your Search was:

Last Name = RYU
First Name = YUNGRYEL

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09128516	6291085	150	08/03/1998	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
09364809	6410162	150	07/30/1999	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
09439529	6342313	150	11/12/1999	OXIDE FILMS AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
09843205	6475825	150	04/26/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
10002790	6610141	150	11/15/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
10615102	Not Issued	030	07/08/2003	PROCESS FOR PREPARING P-N JUNCTIONS HAVING A P-TYPE ZNO FILM	RYU, YUNGRYEL
60406500	Not Issued	159	08/28/2002	HYBRID BEAM DEPOSITION SYSTEM AND METHOD FOR FABRICATING METAL OXIDE ZNO FILMS, P-TYPE ZNO FILMS, AND ZNO - BASED II-VI GROUP COMPOUND SEMICONDUCTOR DEVICES	RYU, YUNGRYEL
60647177	Not Issued	020	01/25/2005	HIGH-PERFORMANCE FET DEVICES AND METHODS	RYU, YUNGRYEL

Inventor Search Completed: No Records to Display.

6,610,141
6,342,313
6,410,162
6,291,085

Search — 438/642, 643, 649
117/8, 54
438/46, 104

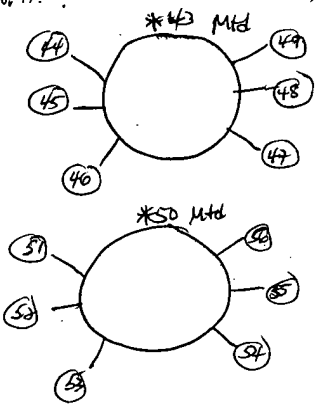
10/615, 102

Examiner's Notes

S(ZnO or zinc(y) oxide)(8a)(film#)
S(Mat(s) acceptor #)(10a)(concentration#)
S(clean?)(6a)(substrate)
S(adjust? or manipulate? or change? or alter?)(8a)(temperature)(6a)(substrate)
S(pulse?)(8a)(laser)
S(p(y) type)(8a)(ZnO)(4a)(film or zinc(a) oxide)(4a)(film#)
S(pellet#)(6a)(press?)(8a)ZnO or press?(8a)zinc(a) oxide)
S(powder#)

112 ¶2 Rej:

Claim 43, line 2, "... net acceptor,.."
Claim 50, line 3, "... net acceptor..."



ODP
U.S. Pat. No. 6,610,141 B2 (White, et al.) claims 1-39.
US. Pat. No. 6,475,825 B2 (White, et al.) claims 1-29,
US. PAT NO. 6,410,162 B1 (White, et al.) claims 1-25
US Pat. No. 6,291,085 B1 (White, et al.) claims 1-30
US. Pat No

8.08 1) [S 1-29 & 72-77 are]
2) [A ZnO film + an oxide film on a substrate]
Group I Prod 3) [433]
4) [338 Å]
5) [S 30-56 Al-71
Group II Mtd 6) [A process for growing a p-type ZnO film comprising Ag on a GaAs substrate]
7)
8)

8.09 1) [S 57-58
Group III Mtd 2) [A process for cleaning a substrate in a chamber]
3) [428]
4) [689+]
8. ~~[S 72-77]~~
Group IV